

N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88 26 April 2019 Product data sheet

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a copper-clip LFPAK88 package. This product has been fully designed and qualified to meet beyond AEC-Q101 requirements delivering high performance and reliability.

2. Features and benefits

- Fully automotive qualified to beyond AEC-Q101:
- -55 °C to +175 °C rating suitable for thermally demanding environments
- LFPAK88 package:
 - Designed for smaller footprint and improved power density over older wire bond packages such as D²PAK for today's space constrained high power automotive applications
 - Thin package and copper clip enables LFPAK88 to be highly efficient thermally
- LFPAK copper clip technology enabling improvements over wire bond packages by:
 - Increased maximum current capability and excellent current spreading
 - Improved R_{DSon}
 - Low source inductance
 - Low thermal resistance R_{th}
- LFPAK Gull Wing leads:
 - Flexible leads enabling high Board Level Reliability absorbing mechanical and thermal cycling stress, unlike traditional QFN packages
 - · Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - Easy solder wetting for good mechanical solder joint
- Unique 40 V Trench 9 superjunction technology:
 - Reduced cell pitch and superjunction platform enables lower R_{DSon} in the same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs

3. Applications

- 12 V automotive systems
- 48 V DC/DC systems (on 12 V secondary side)
- Higher power motors, lamps and solenoid control
- Reverse polarity protection
- LED lighting
- Ultra high performance power switching

4. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Мах | Unit |
|------------------|-------------------------|--|-----|-----|-----|-----|------|
| V _{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 175 °C | | - | - | 40 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | [1] | - | - | 325 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | | - | - | 375 | W |

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| Symbol | Parameter | Conditions | | Min | Тур | Мах | Unit |
|-------------------|----------------------------------|--|-----|------|------|-----|------|
| Static chara | acteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11 | | 0.62 | 0.88 | 1 | mΩ |
| Dynamic ch | naracteristics | | | | | | |
| Q _{GD} | gate-drain charge | I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V; Fig. 13; Fig. 14 | | - | 17 | 34 | nC |
| Source-dra | in diode | | | | | | |
| Qr | recovered charge | | [2] | - | 49 | - | nC |
| S | softness factor | $I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}$ | | - | 0.8 | - | |

[1] 325A continuous current has been successfully demonstrated during application. practically the current will be limited by PCB, thermal design and operating temperature.

[2] includes capacitive recovery

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1 | G | gate | | D |
| 2 | S | source | | |
| 3 | S | source | 0 | G-UFTA) |
| 4 | S | source | | mbb076 S |
| mb | D | mounting base; connected to drain | LFPAK88 (SOT1235) | |

6. Ordering information

| Table 3. Ordering information | | | | | | | |
|-------------------------------|---------|--|---------|--|--|--|--|
| Type number | Package | | | | | | |
| | Name | Description | Version | | | | |
| BUK7S1R0-40H | LFPAK88 | plastic, single-ended surface-mounted package (LFPAK88); 4 leads; 2 mm pitch; 8 mm x 8 mm x 1.6 mm body | SOT1235 | | | | |

7. Marking

| Table 4. Marking codes | |
|------------------------|--------------|
| Type number | Marking code |
| BUK7S1R0-40H | 7S1R040H |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------------|----------------------|---------------------------------|-----|-----|------|
| V _{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 175 °C | - | 40 | V |

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N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88

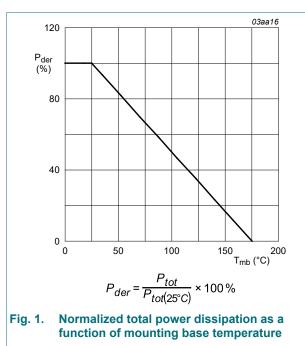
| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|---|---------|-----|------|------|
| V _{GS} | gate-source voltage | DC; T _j ≤ 175 °C | | -10 | 20 | V |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | | - | 375 | W |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | [1] | - | 325 | А |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3 | | - | 1659 | А |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
| Source-drain | diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | [2] | - | 350 | А |
| I _{SM} | peak source current | pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C | | - | 1659 | А |
| Avalanche rug | Igedness | | | | - | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $\label{eq:ID} \begin{array}{l} I_D = 120 \text{ A}; V_{sup} \leq \ 40 \text{V}; \text{R}_{GS} = 50 \Omega; \\ $ | [3] [4] | - | 437 | mJ |

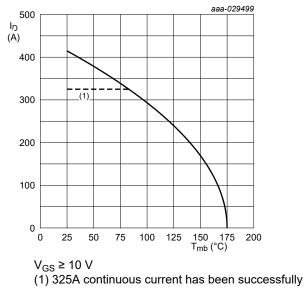
[1] 325A continuous current has been successfully demonstrated during application. practically the current will be limited by PCB, thermal design and operating temperature.

[2] 350Å continuous current has been successfully demonstrated during application. practically the current will be limited by PCB, thermal design and operating temperature.

[3] single pulse avalanche rating limited by maximum junction temperature of 175°C

[4] refer to application note AN10273 for further information

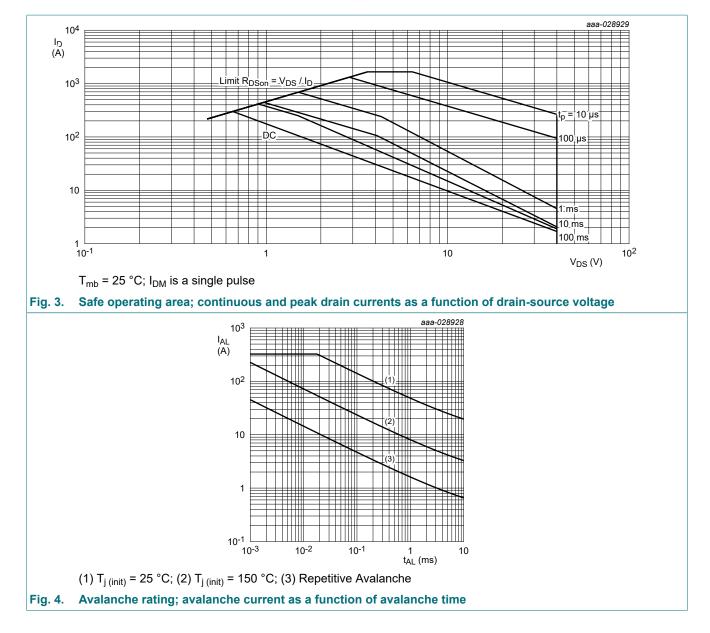




(1) 325A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature

N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK88

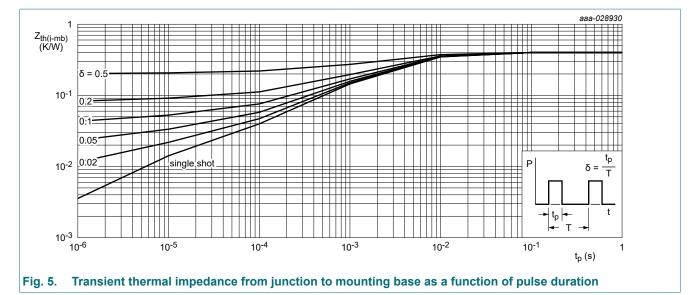


9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|---------------|-----|------|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | <u>Fig. 5</u> | - | 0.35 | 0.4 | K/W |

N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88



10. Characteristics

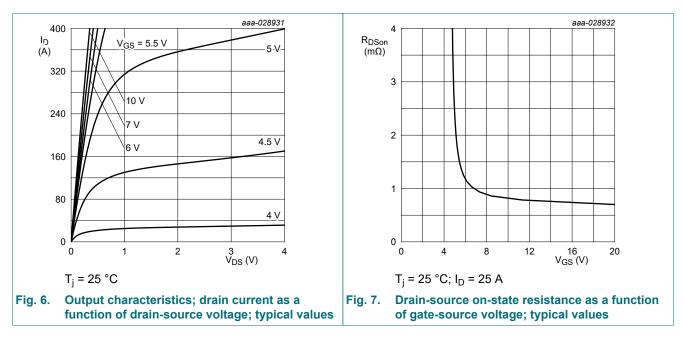
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|-------------------------------------|--|------|------|------|------|
| Static chara | cteristics | · · · | | | | |
| V _{(BR)DSS} | drain-source | I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C | 40 | 43 | - | V |
| | breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C | - | 40.5 | - | V |
| | | I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C | 36 | 40 | - | V |
| V _{GS(th)} | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10 | 2.4 | 3 | 3.6 | V |
| | | I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 10</u> | 1 | - | - | V |
| | | I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C; <u>Fig. 10</u> | - | - | 4.3 | V |
| I _{DSS} | drain leakage current | V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C | - | 0.2 | 1.5 | μA |
| | | V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C | - | 4.7 | 25 | μA |
| | | V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C | - | 287 | 1000 | μA |
| I _{GSS} | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| | | V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11 | 0.62 | 0.88 | 1 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 105 °C; Fig. 12 | 0.87 | 1.3 | 1.6 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 125 °C; Fig. 12 | 0.97 | 1.4 | 1.75 | mΩ |
| | | V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12 | 1.2 | 1.8 | 2.2 | mΩ |
| R _G | gate resistance | f = 1 MHz; T _j = 25 °C | 0.4 | 0.9 | 2.3 | Ω |
| Dynamic ch | aracteristics | | | | | |
| Q _{G(tot)} | total gate charge | I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V; | - | 98 | 137 | nC |
| Q _{GS} | gate-source charge | Fig. 13; Fig. 14 | - | 27 | 40 | nC |
| Q _{GD} | gate-drain charge | | - | 17 | 34 | nC |

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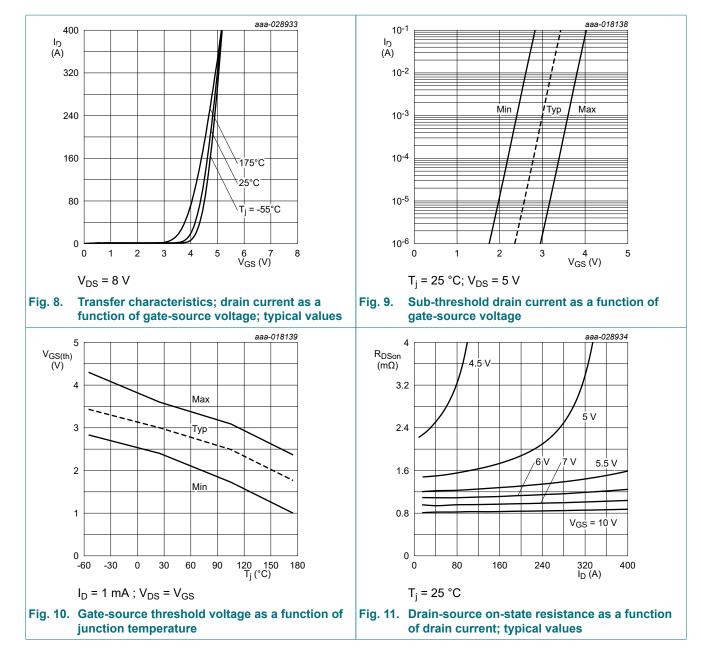
N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------|------------------------------|---|-----|-----|------|-------|------|
| C _{iss} | input capacitance | V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz; | | - | 7373 | 10322 | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 15</u> | | - | 1578 | 2209 | pF |
| C _{rss} | reverse transfer capacitance | | | - | 295 | 649 | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V; | | - | 23 | - | ns |
| t _r | rise time | $R_{G(ext)} = 5 \Omega$ | | - | 19 | - | ns |
| t _{d(off)} | turn-off delay time | | | - | 59 | - | ns |
| t _f | fall time | | | - | 26 | - | ns |
| Source-dra | ain diode | , | | | | | |
| V _{SD} | source-drain voltage | V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u> | | - | 0.76 | 1 | V |
| t _{rr} | reverse recovery time | I _S = 25 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; | | - | 43 | - | ns |
| Q _r | recovered charge | V _{DS} = 20 V | [1] | - | 49 | - | nC |
| S | softness factor | I_{S} = 25 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V; V _{DS} = 20 V; T _j = 25 °C | | - | 0.8 | - | |
| | | $I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -500 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $\text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$ | | - | 0.7 | - | |

[1] includes capacitive recovery

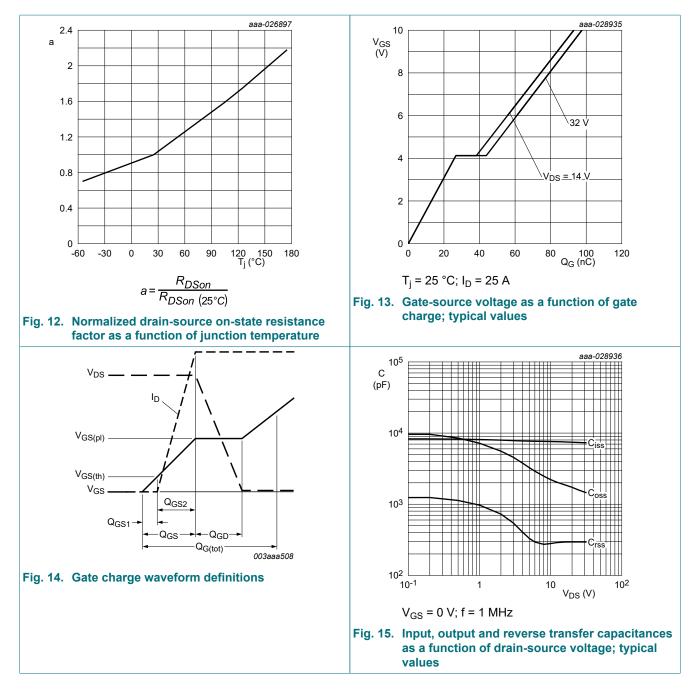


N-channel 40 V, 1.0 mQ standard level MOSFET in LFPAK88

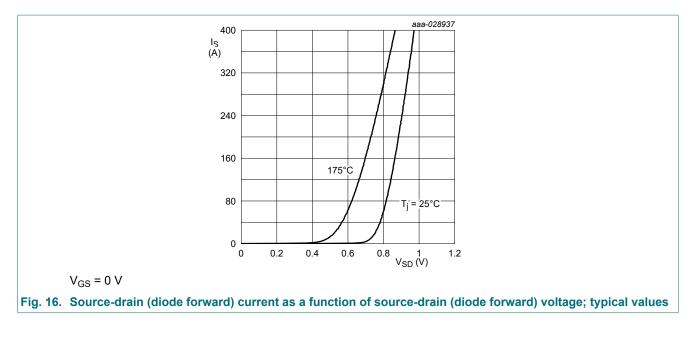


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N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88



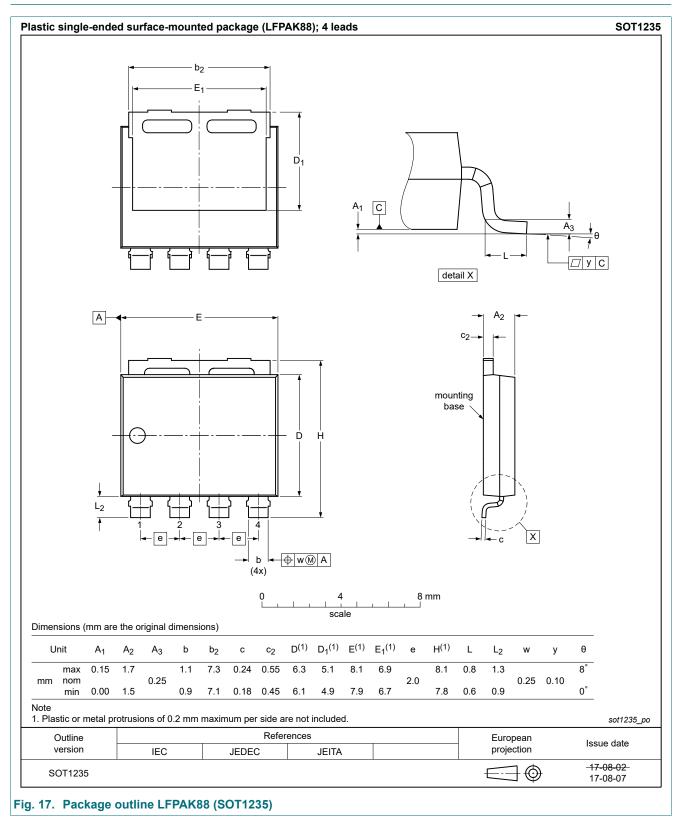
N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK88



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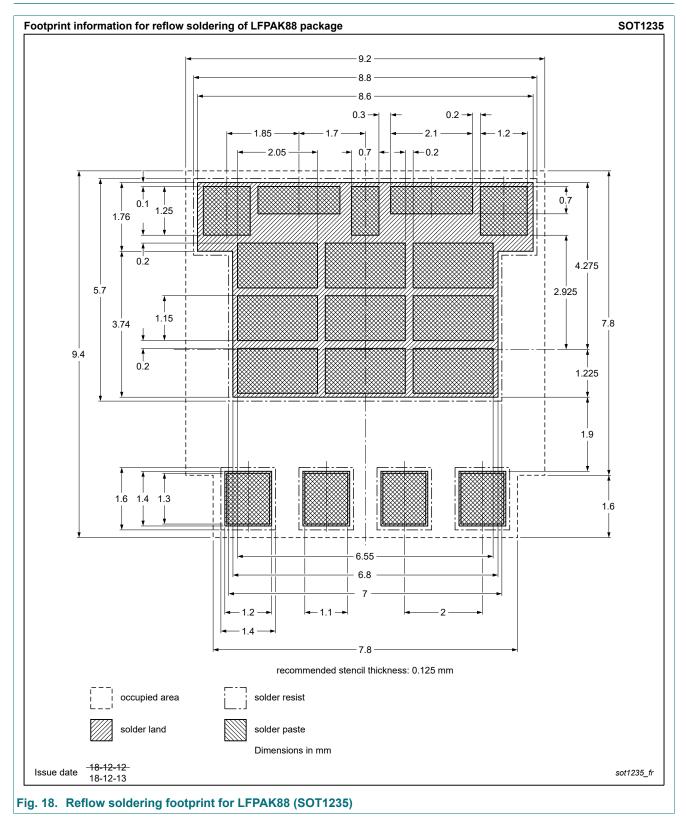
N-channel 40 V, 1.0 mQ standard level MOSFET in LFPAK88

11. Package outline



N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK88

12. Soldering



N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK88

13. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|-----------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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